Czeslaw Skierbiszewski

List of Publications by Year
in descending order

240 papers	3,708 citations	172207 29 h-index	182168 51 g-index
250 all docs	250 docs citations	250 times ranked	2617 citing authors

#	Article	IF	Citations
1	Weak antilocalization and spin precession in quantum wells. Physical Review B, 1996, 53, 3912-3924.	1.1	387
2	Large, nitrogen-induced increase of the electron effective mass in InyGa1â^'yNxAs1â^'x. Applied Physics Letters, 2000, 76, 2409-2411.	1.5	236
3	AlGaN/GaN high electron mobility transistors as a voltage-tunable room temperature terahertz sources. Journal of Applied Physics, 2010, 107, .	1.1	133
4	High electron mobility in AlGaN/GaN heterostructures grown on bulk GaN substrates. Applied Physics Letters, 2000, 77, 2551-2553.	1.5	119
5	Negative differential resistance in dislocation-free GaNâ^•AlGaN double-barrier diodes grown on bulk GaN. Applied Physics Letters, 2006, 88, 172106.	1.5	99
6	Experimental studies of the conduction-band structure of GaInNAs alloys. Semiconductor Science and Technology, 2002, 17, 803-814.	1.0	82
7	Cyclotron resonance and quantum Hall effect studies of the two-dimensional electron gas confined at the GaN/AlGaN interface. Applied Physics Letters, 1997, 70, 2123-2125.	1.5	80
8	Interband optical absorption in free standing layer of Ga0.96In0.04As0.99N0.01. Applied Physics Letters, 2000, 76, 1279-1281.	1.5	68
9	Blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 011114.	1.5	66
10	Band structure and optical properties ofInyGa1â^'yAs1â^'xNxalloys. Physical Review B, 2001, 65, .	1.1	63
11	Effect of Nitrogen-Induced Modification of the Conduction Band Structure on Electron Transport in GaAsN Alloys. Physica Status Solidi (B): Basic Research, 1999, 216, 135-139.	0.7	59
12	High mobility two-dimensional electron gas in AlGaNâ^•GaN heterostructures grown on bulk GaN by plasma assisted molecular beam epitaxy. Applied Physics Letters, 2005, 86, 102106.	1.5	56
13	Nitride-based laser diodes grown by plasma-assisted molecular beam epitaxy. Journal Physics D: Applied Physics, 2014, 47, 073001.	1.3	56
14	Evidence for localized Si-donor state and its metastable properties in AlGaN. Applied Physics Letters, 1999, 74, 3833-3835.	1.5	54
15	Acoustic phonon scattering of two-dimensional electrons in GaN/AlGaN heterostructures. Applied Physics Letters, 2002, 80, 1228-1230.	1.5	51
16	60mW continuous-wave operation of InGaN laser diodes made by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2006, 88, 221108.	1.5	48
17	Nonequivalent atomic step edgesâ€"Role of gallium and nitrogen atoms in the growth of InGaN layers. Journal of Crystal Growth, 2013, 367, 115-121.	0.7	46
18	Nitride-based laser diodes by plasma-assisted MBEâ€"From violet to green emission. Journal of Crystal Growth, 2009, 311, 1632-1639.	0.7	45

#	Article	IF	Citations
19	Optically pumped 500 nm InGaN green lasers grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2011, 110, .	1.1	44
20	True-blue laser diodes with tunnel junctions grown monolithically by plasma-assisted molecular beam epitaxy. Applied Physics Express, 2018, 11, 034103.	1.1	39
21	Effective g* factor of two-dimensional electrons in GaN/AlGaN heterojunctions. Applied Physics Letters, 1999, 75, 3156-3158.	1.5	38
22	Growth optimisation of the GaN layers and GaN/AlGaN heterojunctions on bulk GaN substrates using plasma-assisted molecular beam epitaxy. Physica Status Solidi A, 2004, 201, 320-323.	1.7	36
23	High power blueâ€“violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. Semiconductor Science and Technology, 2005, 20, 809-813.	1.0	36
24	Growth of InGaN and InGaN/InGaN quantum wells by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2008, 310, 3983-3986.	0.7	35
25	The surface boundary conditions in GaN/AlGaN/GaN transistor heterostructures. Applied Physics Letters, 2011, 98, .	1.5	33
26	Beyond Quantum Efficiency Limitations Originating from the Piezoelectric Polarization in Light-Emitting Devices. ACS Photonics, 2019, 6, 1963-1971.	3.2	33
27	InGaN light emitting diodes for 415 nmâ€“520 nm spectral range by plasma assisted MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S917.	0.8	32
28	Enhancement of optical confinement factor by InGaN waveguide in blue laser diodes grown by plasma-assisted molecular beam epitaxy. Applied Physics Express, 2015, 8, 032103.	1.1	32
29	Stack of two III-nitride laser diodes interconnected by a tunnel junction. Optics Express, 2019, 27, 5784.	1.7	32
30	Contactless electroreflectance studies of Fermi level position on c-plane GaN surface grown by molecular beam epitaxy and metalorganic vapor phase epitaxy. Applied Physics Letters, 2012, 100, 181603.	1.5	30
31	Free and bound excitons in GaNâˆ•AlGaN homoepitaxial quantum wells grown on bulk GaN substrate along the nonpolar (112Â¯0) direction. Applied Physics Letters, 2005, 86, 162112.	1.5	29
32	Growth of thin AlInNâˆ•GaInN quantum wells for applications to high-speed intersubband devices at telecommunication wavelengths. Journal of Vacuum Science & Technology B, 2006, 24, 1505.	1.3	29
33	Complete in-plane polarization anisotropy of the A exciton in unstrained A-plane GaN films. Applied Physics Letters, 2007, 91, 141903.	1.5	29
34	Elimination of leakage of optical modes to GaN substrate in nitride laser diodes using a thick InGaN waveguide. Applied Physics Express, 2016, 9, 092103.	1.1	28
35	Control of Mg doping of GaN in RF-plasma molecular beam epitaxy. Journal of Crystal Growth, 2005, 278, 443-448.	0.7	26
36	Contactless electroreflectance of InGaN layers with indium content â‰¤36%: The surface band bending, band gap bowing, and Stokes shift issues. Journal of Applied Physics, 2009, 106, .	1.1	26

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37	Growth mechanism of InGaN by plasma assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 03C136.	0.6	25
38	Hydrogen diffusion in GaN:Mg and GaN:Si. Journal of Alloys and Compounds, 2018, 747, 354-358.	2.8	24
39	Pressure and composition dependence of the electronic structure ofGaAs1â^’xNx. Physical Review B, 2002, 66, .	1.1	23
40	Spin and interaction effects in Shubnikovâ€“de Haas oscillations and the quantum Hall effect in GaN/AlGaN heterostructures. Journal of Physics Condensed Matter, 2004, 16, 3421-3432.	0.7	23
41	The influence of hydrostatic pressure on the formation of a donor superlattice in HgSe:Fe. Semiconductor Science and Technology, 1989, 4, 293-295.	1.0	22
42	Terahertz 3D printed diffractive lens matrices for field-effect transistor detector focal plane arrays. Optics Express, 2016, 24, 20119.	1.7	22
43	Unusual step meandering due to Ehrlich-Schwoebel barrier in GaN epitaxy on the N-polar surface. Applied Surface Science, 2019, 484, 771-780.	3.1	22
44	Effective mass and conduction band dispersion of GaAsN/GaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1078-1081.	1.3	21
45	Role of dislocation-free GaN substrates in the growth of indium containing optoelectronic structures by plasma-assisted MBE. Journal of Crystal Growth, 2007, 305, 346-354.	0.7	20
46	Step-flow anisotropy of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>m</mml:mi></mml:mrow></mml:math>-plane GaN (<mml:math) Tj ETQq0 0 0 rgBT /Overlock 1 growth conditions by plasma-assisted molecular beam epitaxy. Physical Review B, 2	1.1	20
47	Growth mechanisms in semipolar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0020.gif" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mn>2</mml:mn><mml:mspace width=".5em") Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 347 Td <mml:	0.7	20
48	Indium incorporation in semipolar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0010.gif" overflow="scroll"><mml:mrow><mml:mo		

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55	InGaN laser diodes operating at 450â€“460 nm grown by rf-plasma MBE. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 02B102.	0.6	17
56	Vertical Integration of Nitride Laser Diodes and Light Emitting Diodes by Tunnel Junctions. Electronics (Switzerland), 2020, 9, 1481.	1.8	17
57	Blue Laser on High N₂Pressure-Grown Bulk GaN. Acta Physica Polonica A, 2001, 100, 229-232.	0.2	17
58	Bulk GaN crystals grown at high pressure as substrates for blue-laser technology. Physica Status Solidi A, 2003, 200, 9-12.	1.7	16
59	Mode dynamics of high power (InAl)GaN based laser diodes grown on bulk GaN substrate. Journal of Applied Physics, 2007, 101, 083109.	1.1	16
60	AlGaN-Free Laser Diodes by Plasma-Assisted Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 022104.	1.1	16
61	MBE fabrication of III-N-based laser diodes and its development to industrial system. Journal of Crystal Growth, 2013, 378, 278-282.	0.7	16
62	Comparison of the Luminous Efficiencies of Ga- and N-Polar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>In</mml:mi></mml:mrow><mml:mrow><mml:mi>x</mml:mi></mml:m mathvariant="normal">N</mml:mi><mml:mo stretchy="false">/</mml:mo><mml:msub><mml:mrow><mml:mi>In</mml:mi></mml:mrow><mml:mrow>. Physical Review Applied, 2016, 6, .	1.5	16
63	Switching of exciton character in double InGaN/GaN quantum wells. Physical Review B, 2018, 98, .	1.1	16
64	Optical properties of III-nitride laser diodes with wide InGaN quantum wells. Applied Physics Express, 2019, 12, 072003.	1.1	16
65	Optically pumped GaNâˆ•AlGaN separate-confinement heterostructure laser grown along the (112Â¯0) nonpolar direction. Applied Physics Letters, 2007, 90, 081104.	1.5	15
66	Step-flow growth mode instability of N-polar GaN under N-excess. Applied Physics Letters, 2013, 103, .	1.5	15
67	Investigation on the origin of luminescence quenching in N-polar (In,Ga)N multiple quantum wells. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	0.6	15
68	High temperature electrical investigations of (Al,Ga)N/GaN heterostructures - Hall sensor applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1438-1443.	0.8	14
69	Energy difference between electron subbands in AlInNâˆ•GaInN quantum wells studied by contactless electroreflectance spectroscopy. Applied Physics Letters, 2006, 89, 251908.	1.5	14
70	Surface and in-depth characterization of InGaN compounds synthesized by plasma-assisted molecular beam epitaxy. Journal of Alloys and Compounds, 2011, 509, 9565-9571.	2.8	14
71	Determination of gain in AlGaN cladding free nitride laser diodes. Applied Physics Letters, 2013, 103, .	1.5	14
72	Investigation of interface abruptness and In content in (In,Ga)N/GaN superlattices. Journal of Applied Physics, 2016, 120, 125307.	1.1	14

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73	III-nitride optoelectronic devices containing wide quantum wellsâ€"unexpectedly efficient light sources. Japanese Journal of Applied Physics, 2022, 61, SA0801.	0.8	14
74	Mismatch relaxation by stacking fault formation of AlN islands in AlGaN/GaN structures on m-plane GaN substrates. Applied Physics Letters, 2011, 99, 061901.	1.5	13
75	Ultraviolet laser diodes grown on semipolar (202Â¯1) GaN substrates by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	13
76	High power nitride laser diodes grown by plasma assisted molecular beam epitaxy. Journal of Crystal Growth, 2015, 425, 398-400.	0.7	13
77	Transparency of Semi-Insulating, n-Type, and p-Type Ammonothermal GaN Substrates in the Near-Infrared, Mid-Infrared, and THz Spectral Range. Crystals, 2017, 7, 187.	1.0	13
78	Luminescent N-polar (In,Ga)N/GaN quantum wells achieved by plasma-assisted molecular beam epitaxy at temperatures exceeding 700â€‰Â°C. Applied Physics Letters, 2018, 112, .	1.5	13
79	Dependence of InGaN Quantum Well Thickness on the Nature of Optical Transitions in LEDs. Materials, 2022, 15, 237.	1.3	13
80	Plasmon-cyclotron resonance in two-dimensional electron gas confined at the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi><mml:mo>â^•</mml:mo><mml:msub><mml:mi mathvariant="normal">Al</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow><	1.1	12
81	MBE grown GaN/AlGaN lateral Schottky barrier diodes for high frequency applications. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	0.6	12
82	Nitride LEDs and Lasers with Buried Tunnel Junctions. ECS Journal of Solid State Science and Technology, 2020, 9, 015018.	0.9	12
83	Effectiveg*factor in the diluted nitridesGa1â^'yInyNxAs1â^'x. Physical Review B, 2005, 71, .	1.1	11
84	Electron spin resonance and Rashba field in GaN-based materials. Physica B: Condensed Matter, 2011, 406, 2548-2554.	1.3	11
85	Surface properties of c-plane GaN grown by plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	0.6	11
86	Cyan laser diode grown by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2014, 104, 023503.	1.5	11
87	Revealing inhomogeneous Si incorporation into GaN at the nanometer scale by electrochemical etching. Nanoscale, 2020, 12, 6137-6143.	2.8	11
88	Tunnel Junctions with a Doped (<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML") Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 mathvariant="normal">N</mml:mi></mml:mrow></mml:mrow></mml:math> Quantum Well for Vertical Integration of <i>III</i> -Nitride Optoelectronic Devices. Physical Review Applied, 2021, 15, .	1.5	11
89	Waveguide Design for Long Wavelength InGaN Based Laser Diodes. Acta Physica Polonica A, 2012, 122, 1031-1033.	0.2	11
90	Separating strain from composition in unit cell parameter maps obtained from aberration corrected high resolution transmission electron microscopy imaging. Journal of Applied Physics, 2014, 115, 033113.	1.1	10

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91	Theoretical and experimental studies of electric field distribution in N-polar GaN/AlGaN/GaN heterostructures. Applied Physics Letters, 2015, 107, .	1.5	10
92	Bandgap behavior of InGaN/GaN short period superlattices grown by metalâ€organic vapor phase epitaxy. Physica Status Solidi (B): Basic Research, 2017, 254, 1600710.	0.7	10
93	Growth rate independence of Mg doping in GaN grown by plasma-assisted MBE. Journal of Crystal Growth, 2018, 482, 56-60.	0.7	10
94	Dependence of indium content in monolayer-thick InGaN quantum wells on growth temperature in InxGa1-xN/In0.02Ga0.98N superlattices. Journal of Applied Physics, 2018, 124, 065701.	1.1	10
95	Determination of the basic parameters of pseudomorphic GaInAs quantum wells by means of simultaneous transport and optical investigations. Solid-State Electronics, 1994, 37, 665-667.	0.8	9
96	Pressure Studies of Defects and Impurities in Nitrides. Physica Status Solidi (B): Basic Research, 1999, 216, 521-528.	0.7	9
97	Low dislocation density, high power InGaN laser diodes. MRS Internet Journal of Nitride Semiconductor Research, 2004, 9, 1.	1.0	9
98	Influence of dislocation and ionized impurity scattering on the electron mobility in GaN/AlGaN heterostructures. Journal of Crystal Growth, 2005, 281, 194-201.	0.7	9
99	High quality m-plane GaN grown under nitrogen-rich conditions by plasma assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	9
100	Ultraviolet light-emitting diodes grown by plasma-assisted molecular beam epitaxy on semipolar GaN (202Â¯1) substrates. Applied Physics Letters, 2013, 102, .	1.5	9
101	Low frequency noise in two-dimensional lateral GaN/AlGaN Schottky diodes. Applied Physics Letters, 2016, 109, .	1.5	9
102	HVPE-GaN growth on GaN-based Advanced Substrates by Smart Cutâ„¢. Journal of Crystal Growth, 2016, 456, 73-79.	0.7	9
103	Miscut dependent surface evolution in the process of N-polar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0021.gif" overflow="scroll"><mml:mi>GaN</mml:mi><mml:mo>(</mml:mo><mml:mn>000</mml:mn><mml:mover) Tj ETQq1 1 0.784314 rgBT /O growth under N-rich condition. Journal of Crystal Growth, 2017, 457, 38-45.	1.1	9
104	Influence of the growth method on degradation of InGaN laser diodes. Applied Physics Express, 2017, 10, 091001.	1.1	9
105	Extremely long lifetime of III-nitride laser diodes grown by plasma assisted molecular beam epitaxy. Materials Science in Semiconductor Processing, 2019, 91, 387-391.	1.9	9
106	Sensitivity of N-polar GaN surface barrier to ambient gases. Sensors and Actuators B: Chemical, 2019, 281, 561-567.	4.0	9
107	Distributed-feedback blue laser diode utilizing a tunnel junction grown by plasma-assisted molecular beam epitaxy. Optics Express, 2020, 28, 35321.	1.7	9
108	Concentration dependent mobility of two-dimensional electron gas in GaAs/AlGaAs heterostructure. Semiconductor Science and Technology, 1991, 6, 461-464.	1.0	8

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109	AlGaN/GaN HEMTâ€™s photoresponse to high intensity THz radiation. Opto-electronics Review, 2015, 23, .	2.4	8
110	Impact of the substrate lattice constant on the emission properties of InGaN/GaN short-period superlattices grown by plasma assisted MBE. Superlattices and Microstructures, 2019, 133, 106209.	1.4	8
111	Optical properties of N-polar GaN: The possible role of nitrogen vacancy-related defects. Applied Surface Science, 2021, 566, 150734.	3.1	8
112	Nitride light-emitting diodes for cryogenic temperatures. Optics Express, 2020, 28, 30299.	1.7	8
113	Elimination ofDXcenterlike behavior of donors in heavily doped GaAs. Journal of Applied Physics, 1991, 69, 3087-3093.	1.1	7
114	Metastable and nonmetastable deep states of Ge in GaAs. Applied Physics Letters, 1993, 63, 3209-3211.	1.5	7
115	Unusual Behaviour of the DX-Centre in GaAs:Ge. Japanese Journal of Applied Physics, 1993, 32, 218.	0.8	7
116	Twoâ€dimensional electron gas mobility anomalies (and enhancement) in pseudomorphic AlGaAs/InGaAs/GaAs heterostructures. Journal of Applied Physics, 1995, 77, 405-407.	1.1	7
117	Sensitivity of Fermi level position at Ga-polar, N-polar, and nonpolar m-plane GaN surfaces to vacuum and air ambient. Japanese Journal of Applied Physics, 2016, 55, 05FA08.	0.8	7
118	Aluminum-free nitride laser diodes: waveguiding, electrical and degradation properties. Optics Express, 2017, 25, 33113.	1.7	7
119	From High Electron Mobility GaN/AlGaN Heterostructures to Blue-Violet InGaN Laser Diodes. Perspectives of MBE for Nitride Optoelectronics. Acta Physica Polonica A, 2005, 108, 635-651.	0.2	7
120	Ion implantation of tunnel junction as a method for defining the aperture of III-nitride-based micro-light-emitting diodes. Optics Express, 2022, 30, 27004.	1.7	7
121	Factors Governing the Photoluminescence Yield of Erbium Implanted Silicon. Materials Research Society Symposia Proceedings, 1996, 422, 101.	0.1	6
122	Zeeman splitting in GaInNAs. Journal of Physics Condensed Matter, 2004, 16, S3319-S3331.	0.7	6
123	Role of band potential roughness on the luminescence properties of InGaN quantum wells grown by MBE on bulk GaN substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 1614-1618.	0.7	6
124	Doping-Induced Contrast in the Refractive Index for GaInN/GaN Structures at Telecommunication Wavelengths. Applied Physics Express, 2009, 2, 111001.	1.1	6
125	Influence of quantum well inhomogeneities on absorption, spontaneous emission, photoluminescence decay time, and lasing in polar InGaN quantum wells emitting in the blue-green spectral region. Applied Physics A: Materials Science and Processing, 2014, 115, 1015-1023.	1.1	6
126	Strain relaxation in semipolar (202Â¯1) InGaN grown by plasma assisted molecular beam epitaxy. Journal of Applied Physics, 2016, 119, .	1.1	6

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127	A comparative study of semipolar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.gif" overflow="scroll"><mml:mrow><mml:mo stretchy="false">(</mml:mo><mml:mn>2</mml:mn><mml:mspace width="0.12em") Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 747	0.7	6
128	Hydrostatic pressure dependence of indirect and direct excitons in InGaN/GaN quantum wells. Physical Review B, 2020, 101, .	1.1	6
129	Anomalous photocurrent in wide InGaN quantum wells. Optics Express, 2020, 28, 4717.	1.7	6
130	Electrically pumped blue laser diodes with nanoporous bottom cladding. Optics Express, 2022, 30, 10709.	1.7	6
131	Why various types of donor can either enhance or reduce electron mobility in narrow-gap semiconductors. Semiconductor Science and Technology, 1993, 8, S40-S43.	1.0	5
132	Unusual behaviour of the Ge DX centre in GaAs: coexistence of two localized donor states. Journal of Physics Condensed Matter, 1993, 5, 5001-5008.	0.7	5
133	Growth and characterization of AlInN/GaInN quantum wells for high-speed intersubband devices at telecommunication wavelengths. , 2006, , .		5
134	Nitrogen-rich growth for device quality N-polar InGaN/GaN quantum wells by plasma-assisted MBE. Journal of Crystal Growth, 2019, 512, 208-212.	0.7	5
135	Stacking faults in plastically relaxed InGaN epilayers. Semiconductor Science and Technology, 2020, 35, 034003.	1.0	5
136	Far-Infrared Narrow-Band Photodetector Based on Magnetically Tunable Cyclotron Resonance-Assisted Transitions in Pure n-Type InSb. Acta Physica Polonica A, 1997, 92, 733-736.	0.2	5
137	Evolution of dominant light emission mechanism induced by changes of the quantum well width in InGaN/GaN LEDs and LD. Optics Express, 0, , .	1.7	5
138	InGaN blue light emitting micro-diodes with current path defined by tunnel junction. Optics Letters, 2020, 45, 4332.	1.7	5
139	The band structure of mixed-crystal Hg1-xFexSe. Semiconductor Science and Technology, 1993, 8, S22-S25.	1.0	4
140	Photo- and Electroluminescence of Erbium-Doped Silicon. Materials Science Forum, 1997, 258-263, 1509-1514.	0.3	4
141	Observation of quantum Hall effect in 2D-electron gas confined in GaN/GaAlN heterostructure. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 46, 92-95.	1.7	4
142	Far infrared spectroscopy with high resolution cyclotron resonance filters. Journal of Applied Physics, 1998, 84, 433-438.	1.1	4
143	Conduction Band Energy Spectrum of Two-Dimensional Electrons in GaN/AlGaN Heterojunctions. Physica Status Solidi (B): Basic Research, 1999, 216, 719-725.	0.7	4
144	Contactless electroreflectance spectroscopy of interâ€•and intersubâ€band transitions in AlInN/GaInN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 503-507.	0.8	4

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145	Role of Nonequivalent Atomic Step Edges in the Growth of InGaN by Plasma-Assisted Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JE02.	0.8	4
146	Influence of Electric Field on Recombination Dynamics of Quantum Confined Carriers. Acta Physica Polonica A, 2007, 112, 243-247.	0.2	4
147	Electrochemical etching of p-type GaN using a tunnel junction for efficient hole injection. Acta Materialia, 2022, 234, 118018.	3.8	4
148	Shubnikov-de haas effect under hydrostatic pressure in HgSe:Fe. Journal of Crystal Growth, 1990, 101, 869-871.	0.7	3
149	Magnetotransport in high mobility InSbî—¸CdTe heterojunctions: Electric spin-splitting of subbands and high pressure effects. Superlattices and Microstructures, 1991, 9, 51-54.	1.4	3
150	High magnetic field studies of AlGaN/GaN heterostructures grown on bulk GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1355-1359.	0.8	3
151	Comparison of gain in group-III-nitride laser structures grown by metalorganic vapour phase epitaxy and plasma-assisted molecular beam epitaxy on bulk GaN substrates. Semiconductor Science and Technology, 2007, 22, 736-741.	1.0	3
152	Properties of the Two-Dimensional Electron Gas Confined in GaN/AlGaN Interface Studied by Electron Spin Resonance. AIP Conference Proceedings, 2007, , .	0.3	3
153	Contactless electroreflectance of GaInN/AlInN multi quantum wells: The issue of broadening of optical transitions. Microelectronics Journal, 2009, 40, 392-395.	1.1	3
154	Theoretical simulations of radiative recombination time in polar InGaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2273-2275.	0.8	3
155	Broadening of interband transitions in InGaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2282-2284.	0.8	3
156	Trueâ€blue laser diodes grown by plasmaâ€assisted MBE on bulk GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 666-669.	0.8	3
157	Photoluminescence characterization of InGaN/InGaN quantum wells grown by plasmaâ€assisted molecular beam epitaxy: Impact of nitrogen and galium fluxes. Physica Status Solidi (B): Basic Research, 2015, 252, 983-988.	0.7	3
158	Lateral Schottky barrier diodes based on GaN/AlGaN 2DEG for sub-THz detection. , 2016, , .		3
159	Surface potential barrier in m-plane GaN studied by contactless electroreflectance. Applied Physics Express, 2016, 9, 021002.	1.1	3
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